almost equal to the chip size has been developed; and, for example, various types of CSPs are disclosed in "Nikkei Microelement" (pp. 40-64) issued by Nikkei BP, Ltd. (February 1998). CSPs disclosed in this publication are manufactured in such a way that semiconductor elements cut into pieces are bonded onto a polyimide or ceramics substrate on which a wiring layer is formed, and then the wiring layer and semiconductor elements are electrically connected, such as by wire bonding, single point bonding, gang bonding, or bump bonding, and the connections are sealed with resin, after which external terminals such as solder bumps are formed thereon.

IN THE CLAIMS:

Please **amend** claims 1-10, and **add** claims 11-20, as follows:

1. (Amended) A semiconductor device comprising semiconductor elements obtained by cutting a semiconductor wafer having an integrated circuit and an electrode pad formed on one side along a cutting scribe line, a stress cushioning layer installed on said semiconductor elements, a lead wire portion extending from said electrode pad to a top of said stress cushioning layer through an opening formed in said stress cushioning layer on said electrode pad, external electrodes arranged on said lead wire portion on top of said stress cushioning layer, and a conductor protective layer installed on said stress cushioning layer excluding said external electrodes arranged on said lead wire portion, wherein said stress cushioning layer, said lead wire portion, said conductor protective layer, and said external electrodes have means for forming each end face on an end surface of said semiconductor elements inside said cutting scribe line and exposing a range from said end face on said end surface of said semiconductor elements to an inside of said cutting scribe line.